



NCE N-Channel Super Trench Power MOSFET

Description

The NCEP1520K uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

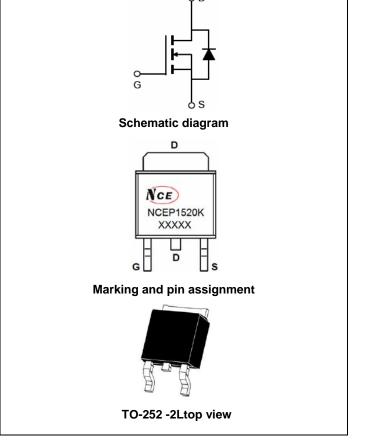
General Features

- V_{DS} =150V,I_D =20A
 - $R_{DS(ON)}$ =59m Ω (typical) @ V_{GS}=10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- LED backlighting
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP1520K	NCEP1520K	TO-252-2L	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	150	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	Ι _D	20	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	14	А
Pulsed Drain Current	I _{DM}	80	А
Maximum Power Dissipation	PD	68	W
Derating factor		0.45	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	65	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{eJC}	2.2	°C/W]
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NCEP1520K

Electrical Characteristics (T_A=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	· ·		•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA			-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V,V _{GS} =0V		-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	· ·		•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.5	3.3	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10A	-	59	65	mΩ
Forward Transconductance	g fs	V_{DS} =5V,I _D =10A	15	-	-	S
Dynamic Characteristics (Note4)	· · ·		•			
Input Capacitance	C _{lss}		-	600		PF
Output Capacitance	C _{oss}	V _{DS} =75V,V _{GS} =0V, F=1.0MHz	-	74.7		PF
Reverse Transfer Capacitance	C _{rss}		-	10.8		PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	9.5	-	nS
Turn-on Rise Time	tr	V_{DD} =75V, RL=7.5 Ω	-	5.5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =3 Ω	-	12.5	-	nS
Turn-Off Fall Time	t _f		-	3	-	nS
Total Gate Charge	Qg		-	12	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =75V,I _D =10A, V _{GS} =10V	-	5.7	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	2.7	-	nC
Drain-Source Diode Characteristics	· ·		•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =10A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	20	А
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C$, $I_F = I_S$	-	29	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	130	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width ≤ 300 μ s, Duty Cycle ≤ 2%.

4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25 $^\circ \!\! \mathbb{C}$,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25\Omega

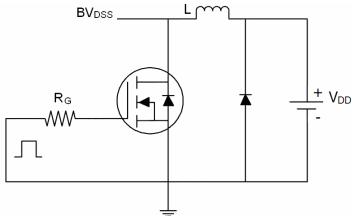


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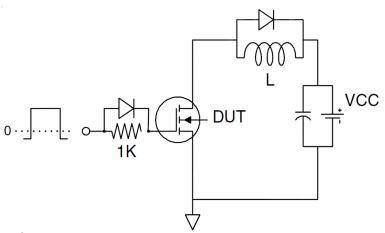




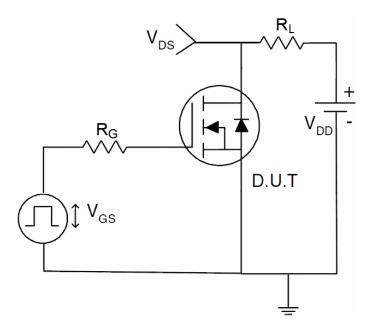
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit



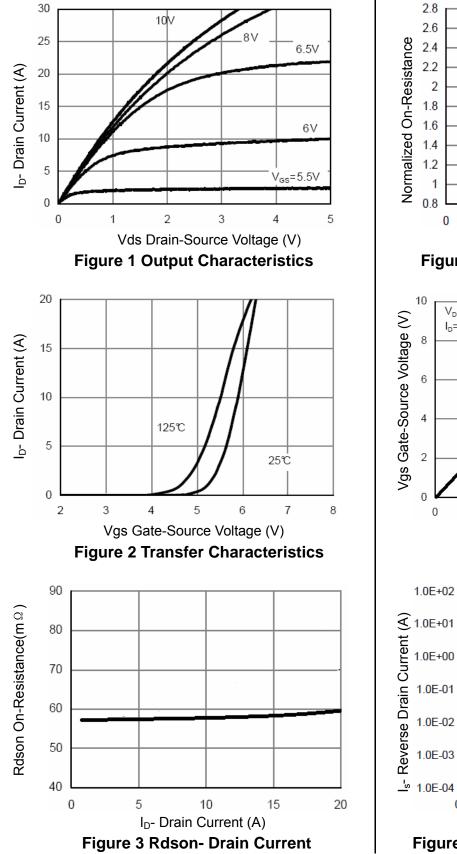
3) Switch Time Test Circuit

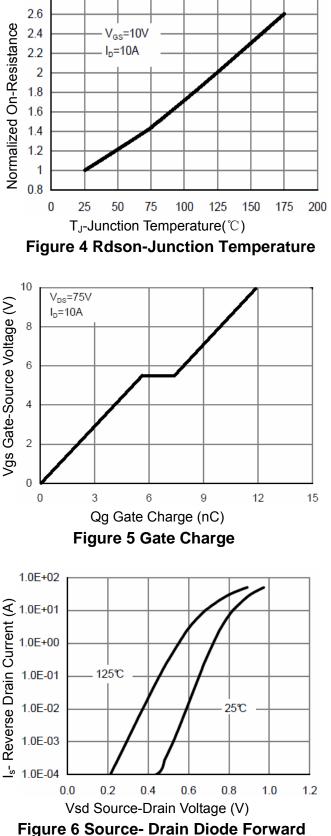














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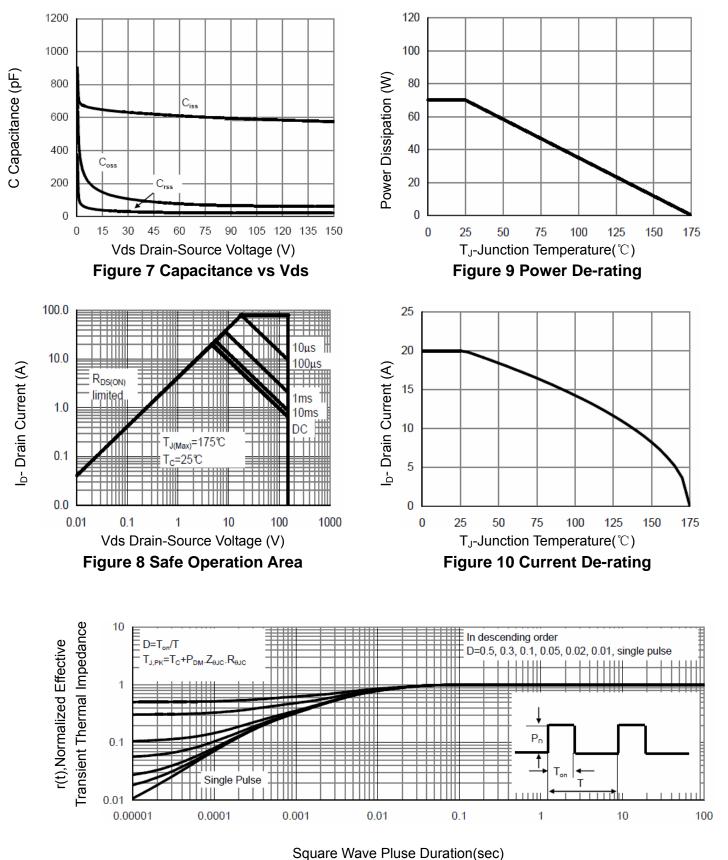


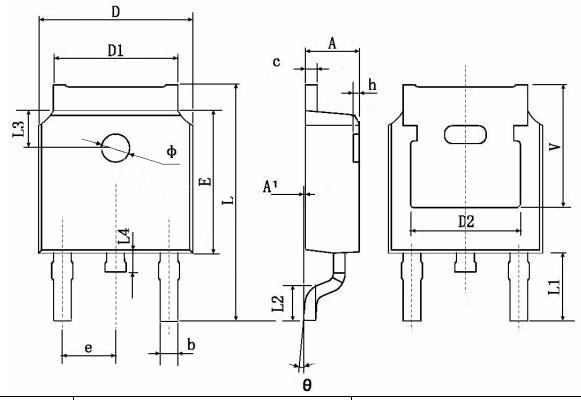
Figure 11 Normalized Maximum Transient Thermal Impedance



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TO-252-2L Package Information



Symbol	Dimensions I	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.83 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900	2.900 TYP.		TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063	TYP.	
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211 TYP.		





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